

Interference Search History MT

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	1	(valence-band adj energy and conduction-band near energy and energy near gap and deep-level). CLM.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/10/24 10:52

EAST - [10654790.wsp:1]

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L1: (68) semiconductor and (valence-band valence adj band) and (conduction-band conduction near b...
 L2: (8) semiconductor and (valence-band near energy valence adj band near energy) and (conduction...
 L3: (8) (valence-band near energy valence adj band near energy) and (conduction-band near energy...
 L4: (8) (valence-band near energy valence adj band near energy) and (conduction-band near energy...

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semiconductor and (valence-band valence adj band) and (conduction-band conduction near band) and energy near gap and (deep near level deep-level) and energy

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050181585 A1	20050818	13	Semiconductor device and manufacturing method of the same	438/514	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20050173728 A1	20050811	21	Nitride heterojunction transistors having charge-transfer induced energy barriers and methods of fabrication the same	257/192	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20050145164 A9	20050707	10	Growth of ultra-high purity silicon carbide crystals in an ambient containing hydrogen	117/84	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20050126471 A1	20050616	29	One hundred millimeter high purity semi-insulating single crystal silicon carbide wafer	117/92	257/E21.324
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20050056864 A1	20050317	27	Use of deep-level transitions in semiconductor devices	257/202	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20050053347 A1	20050310	17	Impurity-based waveguide detectors	385/129	385/40
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20050051767 A1	20050310	17	Embedded waveguide detectors	257/19	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20050006673 A1	20050113	18	Nanowhiskers with PN junctions, doped nanowhiskers, and methods for preparing them	257/232	257/E29.005; 257/E29.341
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20040217343 A1	20041104	18	Material systems for semiconductor tunnel junction structures	257/25	257/103; 257/96; 438/22
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20040209386 A1	20041021	20	Semiconductor laser light source with photocurrent feedback control for single mode operation	438/22	438/29
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20040173788 A1	20040909	29	P-type semiconductor and semiconductor metro material and manufacturing methods thereof	257/12	257/94; 257/E29.093; 438/46